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Atty. Docket No. PLA31223/DBE/US
Serial No: 10/751,212Amendments to the Specification

Please replace the paragraph beginning at page 3, line 26, with the following replacement paragraph:

As shown in Fig. 2, an Au bump 200 is deposited on a bond pad (see bond pad 208 in FIG. 3A) formed on a wafer. The wafer is then diced into a chip 202, which is attached to a substrate 204 by using a thermo-pressure process. An electrical connection of the chip 202 to an external device, i.e., a flip-chip bonding is completed through the thermo-pressure process.

Please replace the paragraph beginning at page 4, line 6, with the following replacement paragraph:

As shown in Fig. 3A, the Au bump 200 formed on bond pad 208 on the chip 202 may be attached to Cu pattern 306 on the substrate 204 through an Ag layer 300 and a Cu layer 302.

Please replace the paragraph beginning at page 4, line 13, with the following replacement paragraph:

Thereafter, the flip-chip bonding is encapsulated by using a nonconductive epoxy and then the substrate 204 is sawed to ~~singulate~~ singulate individual packages.